

# Sen Mei

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1611320/publications.pdf>

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9  
papers

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citations

1937685

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2272923

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docs citations

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times ranked

174  
citing authors

#	ARTICLE	IF	CITATIONS
1	Conductive Atomic Force Microscope Study of Bipolar and Threshold Resistive Switching in 2D Hexagonal Boron Nitride Films. Scientific Reports, 2018, 8, 2854.	3.3	55
2	Boron Vacancies Causing Breakdown in 2D Layered Hexagonal Boron Nitride Dielectrics. IEEE Electron Device Letters, 2019, 40, 1321-1324.	3.9	16
3	New understanding of dielectric breakdown in advanced FinFET devices " physical, electrical, statistical and multiphysics study. , 2016, , .		8
4	Area and pulsewidth dependence of bipolar TDDB in MgO magnetic tunnel junction. , 2018, , .		7
5	Stochastic Modeling of FinFET Degradation Based on a Resistor Network Embedded Metropolis Monte Carlo Method. IEEE Transactions on Electron Devices, 2018, 65, 440-447.	3.0	6
6	Impact of Carbon Doping on Polysilicon Grain Size Distribution and Yield Enhancement for 40-nm Embedded Nonvolatile Memory Technology. IEEE Transactions on Device and Materials Reliability, 2018, 18, 64-69.	2.0	4
7	Multiphysics based 3D percolation framework model for multi-stage degradation and breakdown in high- $\epsilon_r$ Interfacial layer stacks. , 2016, , .		2
8	Statistical basis and physical evidence for clustering model in FinFET degradation. , 2017, , .		2
9	Reliability and Breakdown Study of Erase Gate Oxide in Split-Gate Non-Volatile Memory Device. , 2020, , .		0